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customized optoelectronics



EPIGAP
OPTRONIC GMBH

Product Data Sheet

Preliminary

LED Chip UV

EOLC-375-34

Rev. 01 aus 2011

Radiation	Type	Electrodes
Ultra violet		P + N up

<p style="text-align: center;">Unit : μm</p>	<p>Description</p> <ul style="list-style-type: none"> -Substrate: Sapphire, epitaxial layer: GaN based Material -N bonding pad electrode: Au alloy -P bonding pad electrode: Au alloy -Emission area: $201 \mu\text{m} \times 201 \mu\text{m}$ -Bottom area: $280 \mu\text{m} \times 280 \mu\text{m} \pm 20 \mu\text{m}$ -Chip thickness: $120 \mu\text{m} \pm 10 \mu\text{m}$ -Bonding pad electrodes: (each) $90 \mu\text{m}$ -Electrodes spacing: $128 \mu\text{m} \pm 5 \mu\text{m}$
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Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20\text{mA}$	V_F	3.2	3.6	4.2	V
Reverse current	$V_R = 5\text{V}$	I_R			10	μA
Peak wavelength	$I_F = 20\text{mA}$	λ_p	375		380	nm
Full width at half maximum	$I_F = 20\text{mA}$	$\Delta\lambda$		12		nm
Optical power output	$I_F = 20\text{mA}$	P_o	2.5		5.5	mW

Spectrum

